

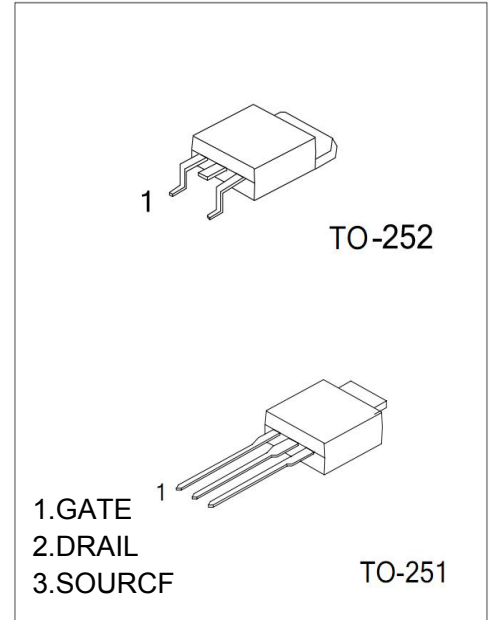


# MKD210

## N-Channel 30-V(D-S) Power MOSFET

V(BR)DSS	RDS(on)MAX	ID
30 V	3 mΩ@ 10 V	70A
	4 mΩ@ 4.5 V	

### Equivalent Circuit:



### General Description:

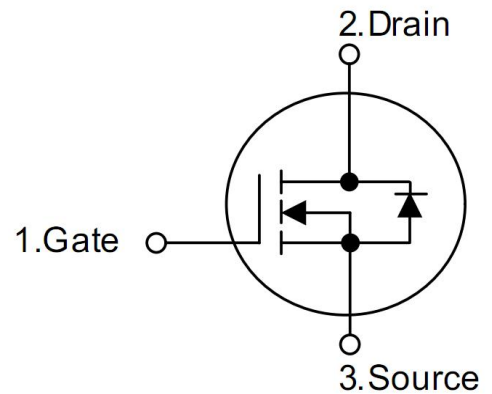
The MKD210 uses Trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance. Power losses are minimized due to an extremely low combination of RDS(ON) and Crss. In addition, switching behavior is well controlled with a “Schottky style” soft recovery body diode.

**MARKING:** MKD210 MKD / U \*\*\*\*  
(D-252) / (U-251)

### FEATURE:

- ※ 100% Rg Tested
- ※ 100% UIS Tested

### SYMBOL:



### Maximum ratings ( Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	VGS	±20	
Continuous Drain Current	ID	70	A
Pulsed Diode Curren	IDM	390	
Power Dissipation	PD	50	W
Thermal Resistance from Junction to Ambient (t≤10s)	RθJA	100	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	



**MOSFET ELECTRICAL CHARACTERISTICS**

**Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)**

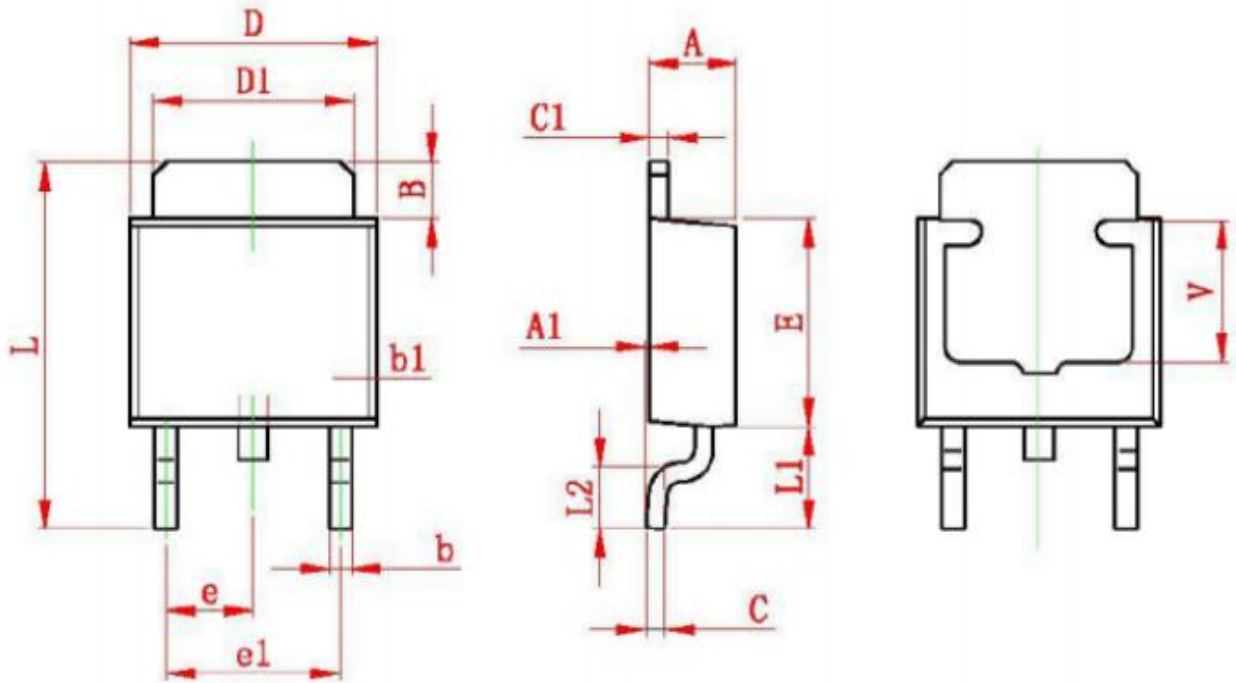
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = 250μA	30			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = 250μA	1		2.2	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±20V			±100	nA
Zero gate voltage drain current	IDSS	VDS = 30V, VGS =0V			1	μA
Drain-source on-state resistancea	RDS(on)	VGS = 10V, ID = 20A		2.4	3	mΩ
		VGS = 4.5V, ID = 20A		3	4	mΩ
Forward transconductancea	gfs	VDS = 5V, ID = 20A		78		S
Diode forward voltage	VSD	IS= 2A, VGS=0V		0.8	1.2	V
<b>Dynamic</b>						
Input capacitance	Ciss	VDS = 15V, VGS =0V, f=1MHz		3520		pF
Output capacitance	Coss			1320		pF
Reverse transfer capacitanceb	Crss			90		pF
Total gate charge	Qg	VDS = 15V, VGS = 10V, ID = 20A		48		nC
Gate-source charge	Qgs			9		nC
Gate-drain charge	Qgd			7		nC
<b>Switchingb</b>						
Turn-on delay time	td(on)	VDS= 15V RL= 1Ω, ID = 20A, VGEN= 10V, Rg= 3Ω		11		ns
Rise time	tr			10		ns
Turn-off delay time	td(off)			38		ns
Fall time	tf			10		ns
<b>Drain-Source Diode Characteristics</b>						
Continuous Source-Drain Diode Current	IS				70	A
Pulsed Diode forward Curren	ISM				200	A

**Note :**

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 10 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.



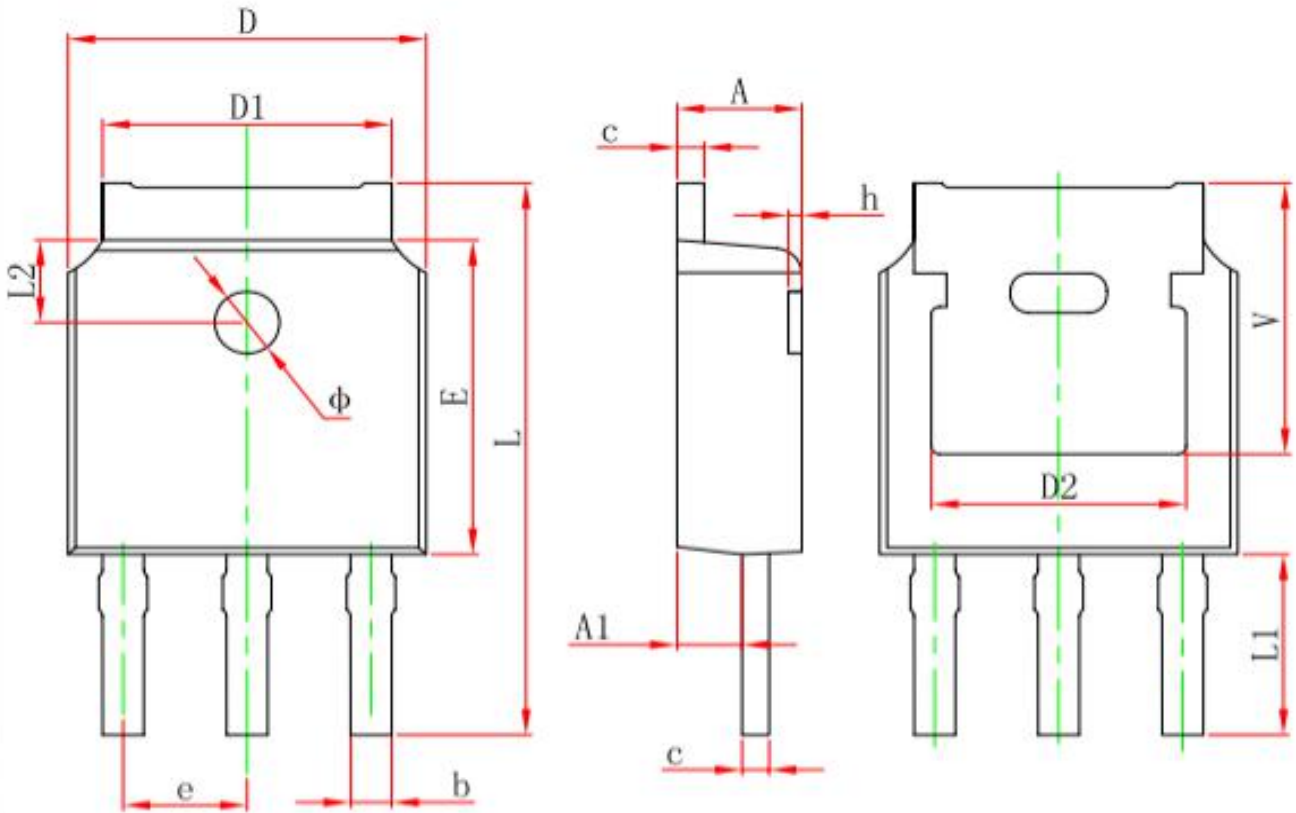
PACKAGE OUTLINE DIMENSIONS :



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP		0.091 TYP	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
V	3.80 REF		0.150 REF	



PACKAGE OUTLINE DIMENSIONS :



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.860	1.160	0.034	0.046
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	10.400	11.000	0.409	0.433
L1	3.300	3.700	0.130	0.146
L2	1.600 REF.		0.063 REF.	
$\Phi$	1.100	1.300	0.043	0.051
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	